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 Signature	

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
David Becker et al.

Serial No.: 09/923,058

Filed: 8/6/01

For: METHODS FOR ENHANCING SILICON
DIOXIDE TO SILICON NITRIDE
SELECTIVITY (*as previously amended*)

Group Art Unit: 1763

Examiner: George Goudreau

Examiner phone: 571-272-1434

Atty. Dkt. No.: 102-0072US-4

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria VA, 22313-1450

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, it is respectfully requested that this Information Disclosure Statement (IDS) be entered and the documents listed on attached Form PTO-1449 be considered by the Examiner and made of record. Copies of the listed documents are attached.

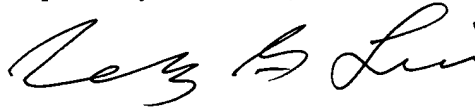
In accordance with 37 C.F.R §§ 1.97(g),(h), this IDS is not to be construed as a representation that a search has been made, and is not to be construed to be an admission that the information cited is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b), or that such information constitutes prior art.

As these references were not submitted with the Applicant's most recent IDS, the numbering of the listed references on the attached Form 1449 continues from the numbering used in the Information Disclosure Statement previously submitted on June 10, 2004.

This IDS is being filed after a first office action on the merits, but before the close of prosecution. Accordingly, a fee of \$180.00 is believed due. ***This Office is authorized to deduct this fee, and any other necessary fees, from Deposit Account No. 501922, referencing matter no. 102-0072US-4.***

Applicant respectfully requests that the listed documents be considered and made of record in the present case, and that the Examiner initial the appropriate spaces on the Form 1449 to evidence the same.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Terril G. Lewis".

Terril G. Lewis, Reg. No. 46,065

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Form PTO-1449 (modified)	Atty. Docket No. 102-0072US-4	Serial No. 09/923,058
List of Patents and Publications for Applicant's INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Inventor/Applicant: Becker, et al. / Micron Technology, Inc.	
	Title: METHODS FOR ENHANCING SILICON DIOXIDE TO SILICON NITRIDE SELECTIVITY (as previously amended)	
	Filing Date: 08/06/01	Group: 1763

U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
	A1						

Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1						

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
	C77	Various Japanese abstracts (untranslated) 8p-P-14, 8p-P-15, 8a-R-1
	C78	Various Japanese abstracts (untranslated) 7p-T-14, 7p-T-15, 7p-T-16
	C79	H. Enomoto & T. Tokunaga, "Analysis of Mechanisms of Highly Selective Oxide Etching," 1994 Dry Process Symposium, pp. 241-46 (Nov. 10-11, 1994, Tokyo).
	C80	Y. Gotoh & T. Kure, "Analysis of Polymer Formation During SiO ₂ Microwave Plasma Etching," 1994 Dry Process Symposium, pp. 211-16 (Nov. 10-11, 1994, Tokyo).
	C81	Y. Hikosaka et al., "Inductively-Coupled Plasma Etching in a Pulsed Mode," 1994 Dry Process Symposium, pp. 199-204 (Nov. 10-11, 1994, Tokyo).
	C82	K. Kurihara et al., "Measurement of Energy Distribution of Ion Species Through a High-Aspect-Ratio Hole in a C ₄ F ₈ Plasma," 1994 Dry Process Symposium, pp. 217-221 (Nov. 10-11, 1994, Tokyo).
	C83	Shin Arai, "Polymer Deposition Control in SiO ₂ Etching by Substrate Temperature Manipulation," 1994 Dry Process Symposium, pp. 223-227 (Nov. 10-11, 1994, Tokyo).
	C84	

EXAMINER:	DATE CONSIDERED:
EXAMINER: INITIAL IF REFERENCE CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	